74AUP1G00

Low-power 2-input NAND gate

Rev. 7 — 23 April 2019

Product data sheet

1. General description

The 74AUP1G00 provides the single 2-input NAND function.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- · High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74AUP1G00GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1			
74AUP1G00GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886			
74AUP1G00GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891			
74AUP1G00GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115			
74AUP1G00GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202			
74AUP1G00GX	-40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.35 mm	SOT1226			

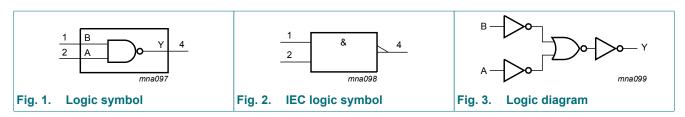
4. Marking

Table 2. Marking

Type number	Marking code [1]
74AUP1G00GW	рА
74AUP1G00GM	рА
74AUP1G00GF	рА
74AUP1G00GN	рА
74AUP1G00GS	рА
74AUP1G00GX	рА

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

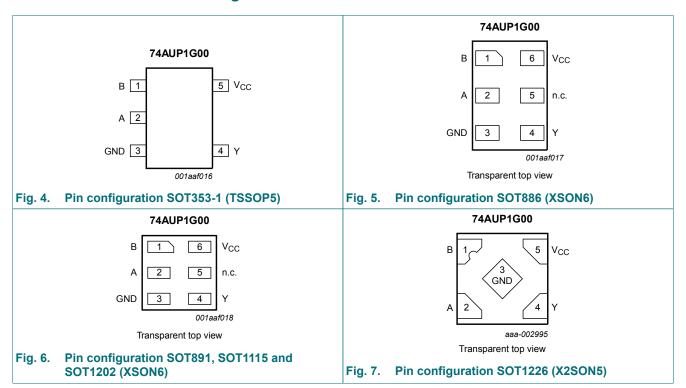
5. Functional diagram



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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Pin		
	TSSOP5 and X2SON5	XSON6		
В	1	1	data input	
Α	2	2	data input	
GND	3	3	ground (0 V)	
Υ	4	4	data output	
n.c.	-	5	not connected	
V _{CC}	5	6	supply voltage	

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7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$

Input		Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
Vo	output voltage	Active mode	[1]	-0.5	V _{CC} + 0.5	V
		Power-down mode	[1]	-0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$		-	±20	mA
I _{CC}	supply current			-	+50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V; } V_{CC} = 0 \text{ V}$	-	-	±0.2	μA
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	$V_1 = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V} $ [1]	-	-	40	μA
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	8.0	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		$I_{\rm O}$ = -2.3 mA; $V_{\rm CC}$ = 2.3 V	1.97	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
lį	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V} $ [1]	-	-	50	μA
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1]	-	-	75	μA

^[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 9

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
T _{amb} = 2	5 °C; C _L = 5 pF					
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 8</u> [2]				
		V _{CC} = 0.8 V	-	17.5	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	5.3	11.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	6.8	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.3	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	2.5	4.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.2	3.6	ns

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Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
T _{amb} = 2	25 °C; C _L = 10 pF					
t _{pd}	propagation delay	A, B to Y; see Fig. 8	2]			
		V _{CC} = 0.8 V	-	21.0	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	6.1	13.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.4	4.4	7.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.7	6.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	3.0	4.7	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.8	4.3	ns
T _{amb} = 2	25 °C; C _L = 15 pF	,				
t _{pd}	propagation delay	A, B to Y; see Fig. 8	2]			
		V _{CC} = 0.8 V	-	24.5	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	6.9	14.8	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	8.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	3.5	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	3.2	4.9	ns
T _{amb} = 2	25 °C; C _L = 30 pF	,				
t _{pd}	propagation delay	A, B to Y; see Fig. 8	2]			
		V _{CC} = 0.8 V	-	34.8	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.6	9.2	20.1	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	6.5	11.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	5.4	9.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	4.6	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	4.3	6.5	ns
T _{amb} = 2	5 °C	,				
C _{PD}	power dissipation	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	B]			
	capacitance	V _{CC} = 0.8 V	-	2.6	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.8	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	2.9	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	3.1	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	3.6	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	4.2	-	pF
	1					

^[1] All typical values are measured at nominal V_{CC} .

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

 ^[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

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Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 9

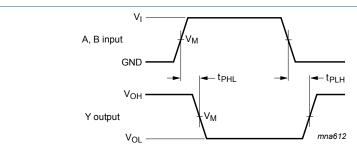
Symbol	Parameter	Conditions	-40 °C 1	to +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
C _L = 5 p	F						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 8</u> [1]				
		V _{CC} = 1.1 V to 1.3 V	2.1	12.2	2.1	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	1.8	7.8	1.8	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.4	6.2	1.4	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.1	4.7	1.1	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	4.2	1.0	4.7	ns
C _L = 10	pF						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 8</u> [1]				
		V _{CC} = 1.1 V to 1.3 V	2.2	14.4	2.2	15.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	9.2	2.2	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	7.3	1.9	8.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	5.6	1.3	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.2	4.9	1.2	5.4	ns
C _L = 15	pF						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 8</u> [1]				
		V _{CC} = 1.1 V to 1.3 V	3.1	16.5	3.1	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	10.5	2.5	11.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	8.3	2.0	9.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	6.4	1.5	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	5.7	1.4	6.3	ns
C _L = 30	pF						•
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 8</u> [1]				
		V _{CC} = 1.1 V to 1.3 V	4.1	22.6	4.1	24.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	14.0	2.9	15.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	11.1	2.3	12.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	8.5	2.1	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	7.6	2.1	8.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

Product data sheet

Low-power 2-input NAND gate

11.1. Waveforms and test circuit



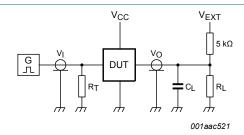
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig. 8. The data input (A or B) to output (Y) propagation delays

Table 10. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _I	$t_r = t_f$	V _M
0.8 V to 3.6 V	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns	0.5 × V _{CC}



Test data is given in Table 11.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig. 9. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V _{EXT}			
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	2 × V _{CC}	

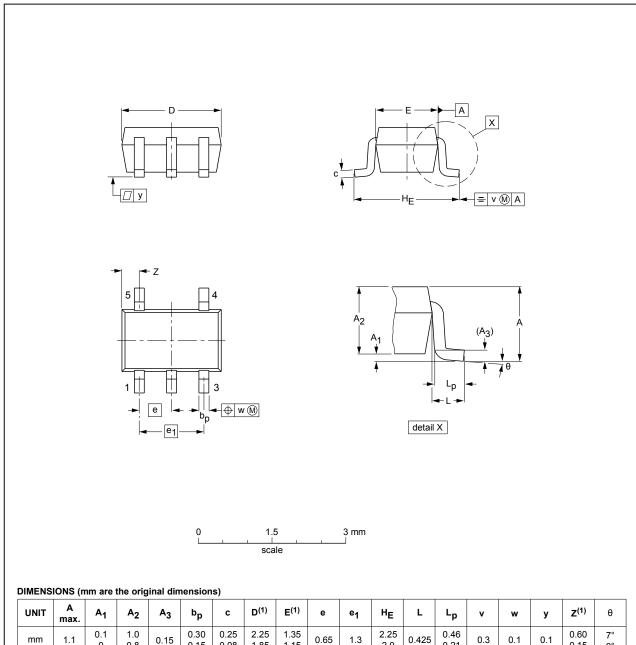
[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

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12. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	HE	L	Lp	٧	w	у	Z ⁽¹⁾	θ	
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°	

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE			REFER	EUROPEAN	ISSUE DATE			
VEF	RSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SO ⁻	T353-1		MO-203	SC-88A			-00-09-01 03-02-19	

Fig. 10. Package outline SOT353-1 (TSSOP5)

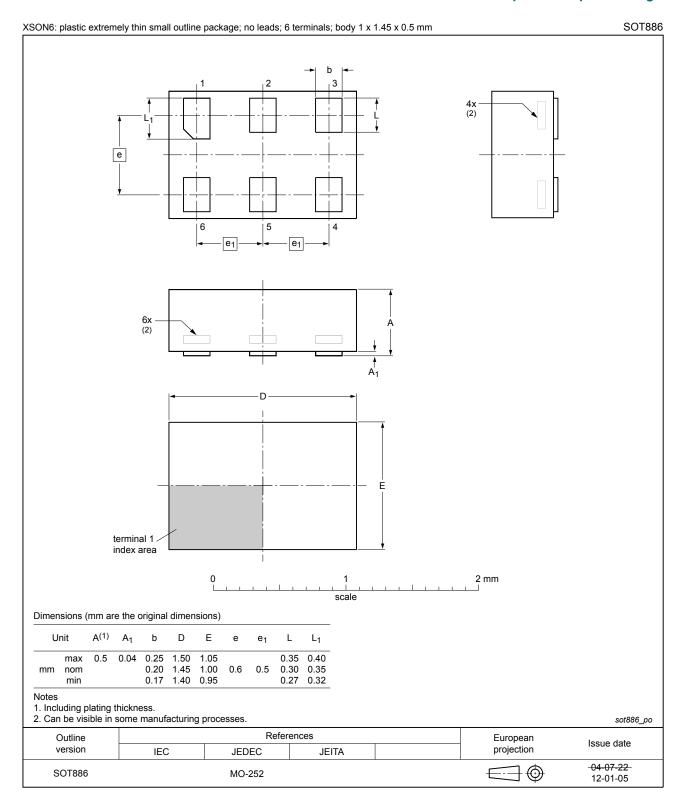


Fig. 11. Package outline SOT886 (XSON6)

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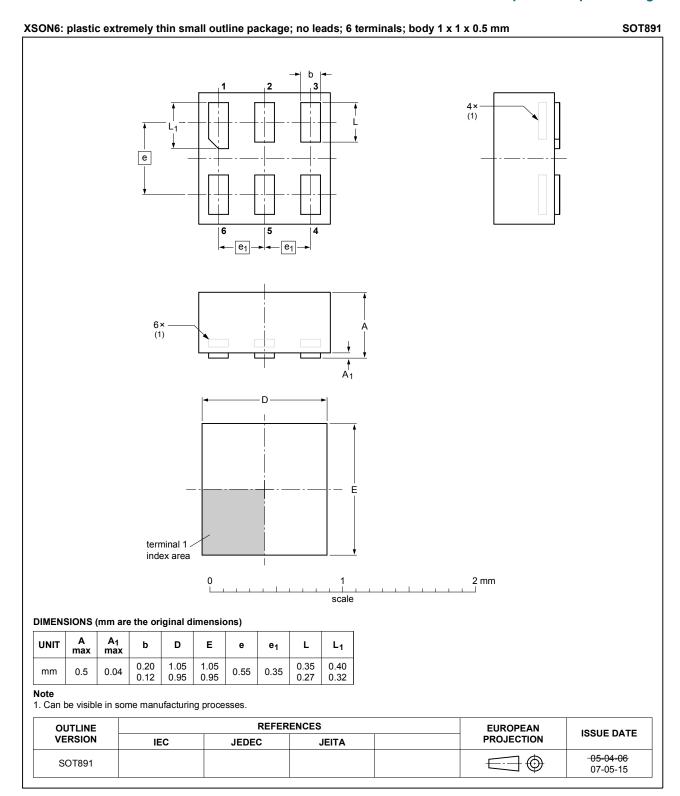


Fig. 12. Package outline SOT891 (XSON6)

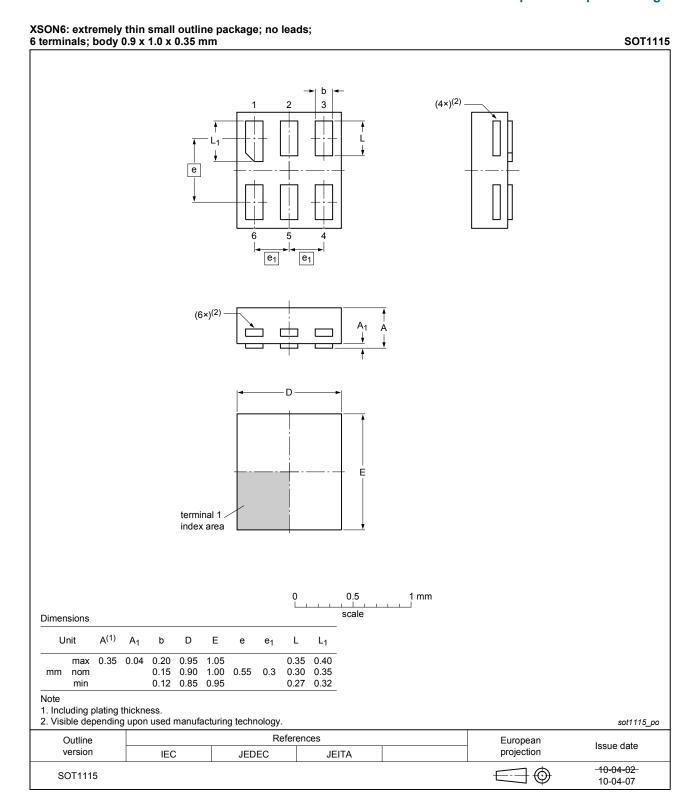


Fig. 13. Package outline SOT1115 (XSON6)

Low-power 2-input NAND gate

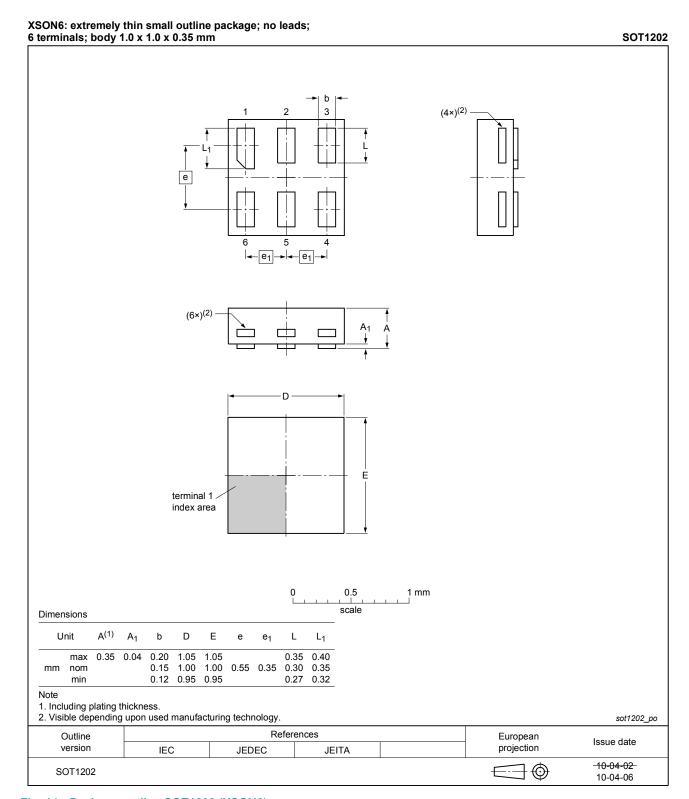


Fig. 14. Package outline SOT1202 (XSON6)

Product data sheet

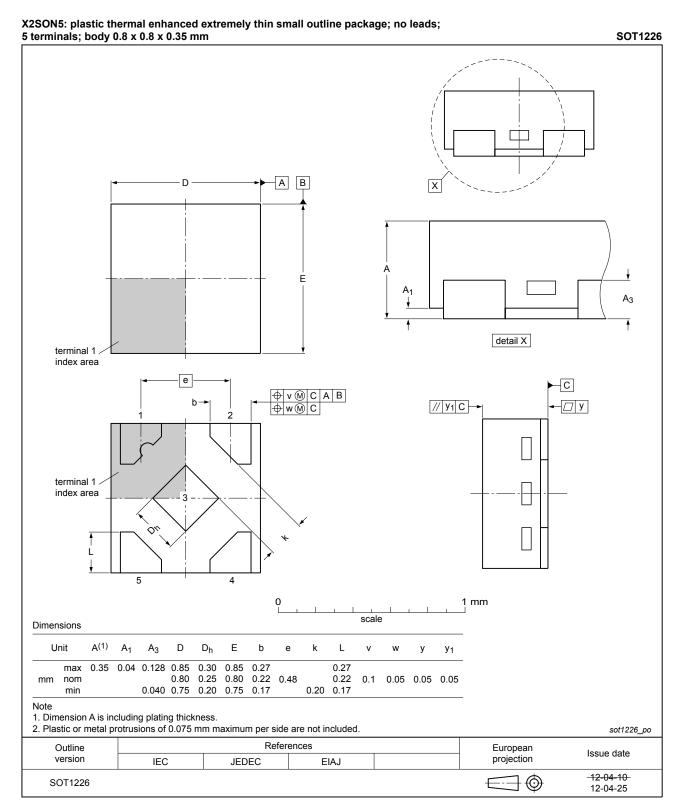


Fig. 15. Package outline SOT1226 (X2SON5)

Low-power 2-input NAND gate

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
74AUP1G00 v.7	20190423	Product data sheet	-	74AUP1G00 v.6			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guid of Nexperia. Legal texts have been adapted to the new company name where appropriate. Pin configuration drawing (Fig. 7) SOT1226 (X2SON5) updated. 						
74AUP1G00 v.6	20120627	Product data sheet	-	74AUP1G00 v.5			
Modifications:	Added type r	number 74AUP1G00GX (So	OT1226).				
74AUP1G00 v.5	20120316	Product data sheet	-	74AUP1G00 v.4			
Modifications:	Package outl	ine drawing of SOT886 (Fig	g. 11) modified.				
74AUP1G00 v.4	20111115	Product data sheet	-	74AUP1G00 v.3			
Modifications:	 Legal pages 	updated.					
74AUP1G00 v.3	20101007	Product data sheet	-	74AUP1G00 v.2			
74AUP1G00 v.2	20060629	Product data sheet	-	74AUP1G00 v.1			
74AUP1G00 v.1	20050711	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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